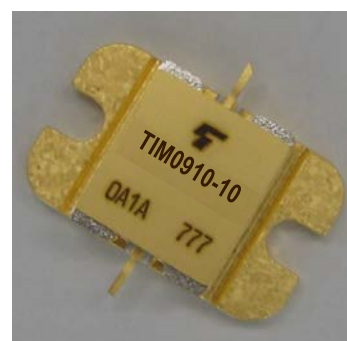


FEATURES

- BROAD BAND INTERNALLY MATCHED FET
- HIGH POWER
P1dB= 40.0dBm at 9.5GHz to 10.5GHz
- HIGH GAIN
G1dB= 6.0dB at 9.5GHz to 10.5GHz
- HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 9V IDSSet= 4.0A f = 9.5 to 10.5GHz	dBm	40.0	40.5	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	5.0	6.0	—
Drain Current	IDSS		A	—	4.0	5.0
Power Added Efficiency	η_{add}		%	—	23	—
Channel Temperature Rise	ΔT_{ch}		(VDS X IDSS + Pin – P1dB) X Rth(c-c)	°C	—	—

Recommended Gate Resistance(Rg): 100 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

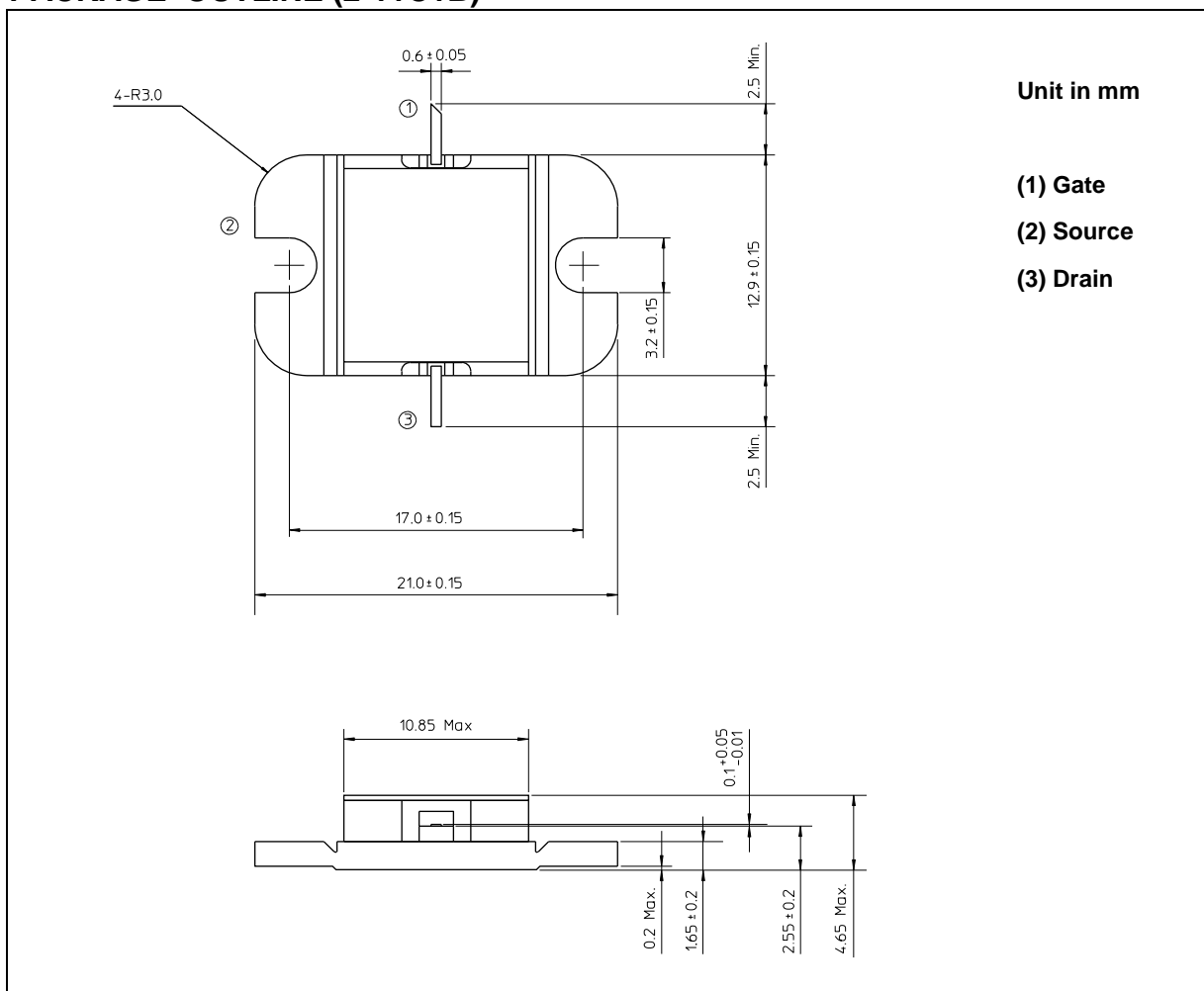
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDSS= 4.8A	S	—	3.0	—
Pinch-off Voltage	VGSoff	VDS= 3V IDSS= 145mA	V	-1.5	-3.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	10.0	—
Gate-Source Breakdown Voltage	VGSO	IGS= --145 μ A	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	2.0	2.5

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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	11.5
Total Power Dissipation (Tc= 25°C)	PT	W	60
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-11C1B)

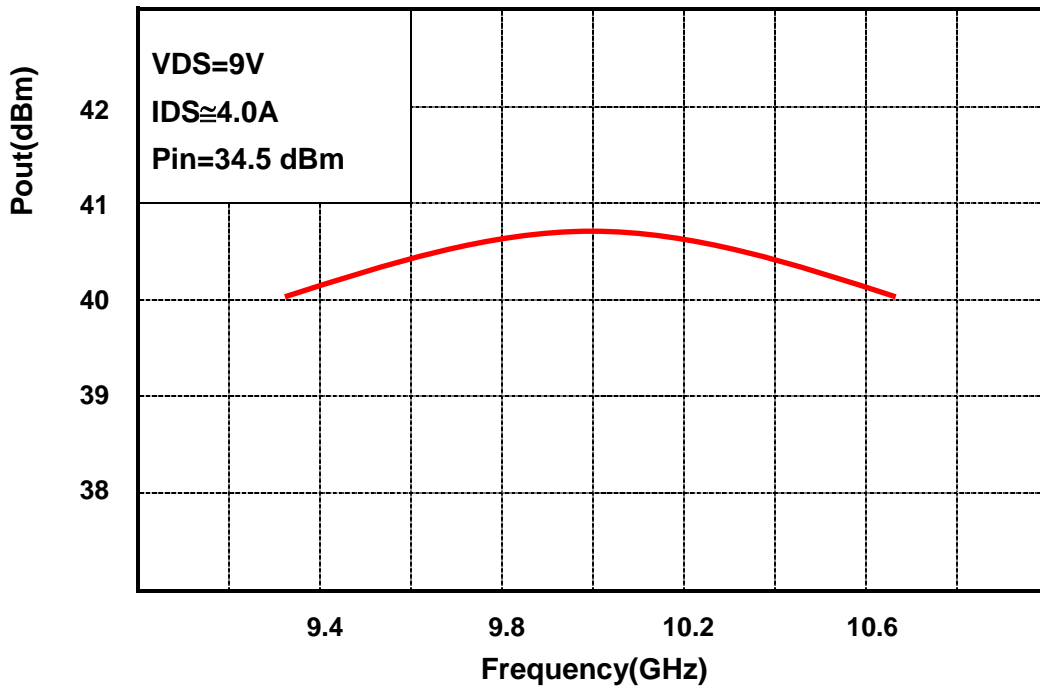


HANDLING PRECAUTIONS FOR PACKAGE MODEL

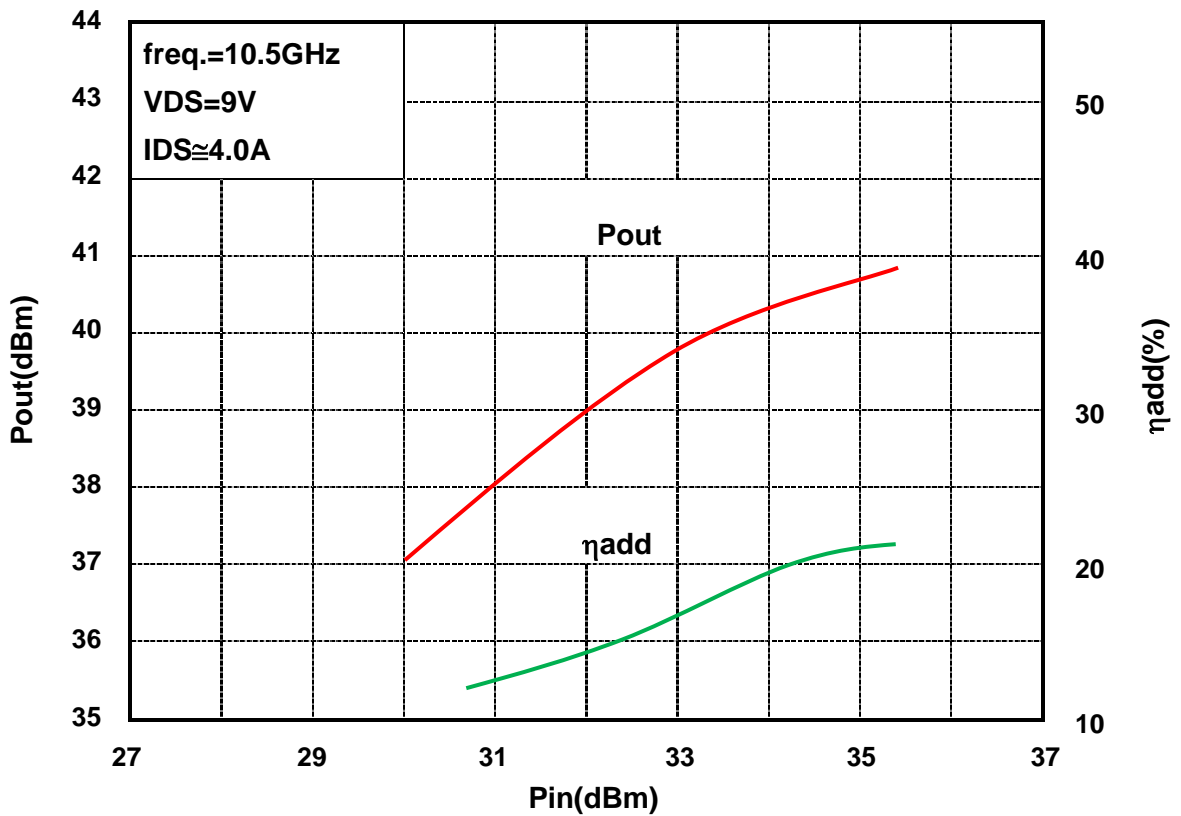
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

RF PERFORMANCE

Output Power (Pout) vs. Frequency



Output Power(Pout) vs. Input Power(Pin)



Power Dissipation(PT) vs. Case Temperature(Tc)

